

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
--	----------	---	----

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	10

ORDERING INFORMATION

J	ST	02	V	-1000	SW
JieJie Microelectronics Co., Ltd.	Triacs				
					SW:IGT1-3 1000:V _{DRM} /V _{RRM} 1000V

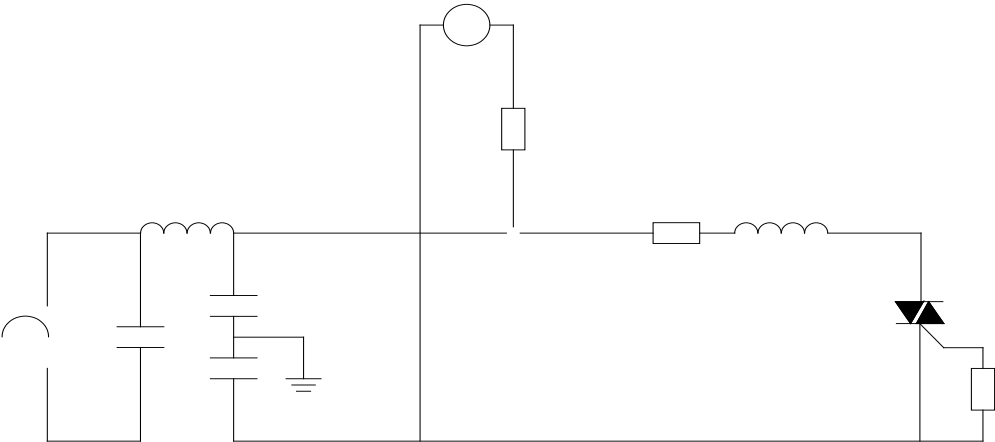
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



JST02V-1000SW

JieJie M

PACKAGE MECHANICAL DATA

Dimensions

MMB37 ()13I

JST0

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.



is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.